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A Product Line of Diodes Incorporated

Case Material: Molded Plastic, "Green" Molding Compound.



#### 240V P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

UL Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020

Terminals: Matte Tin Finish (@3)

Weight: 0.052 grams (approximate)

#### **Features**

- BV<sub>DSS</sub> > -240V
- R<sub>DS(on)</sub> ≤ 8.8Ω @ V<sub>GS</sub> = -3.5V
- Low threshold and Fast switching
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

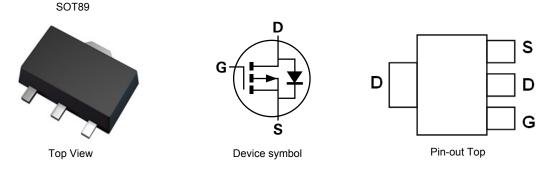
## Application

- Electronic hook switches
- Telecoms and Battery powered equipment



**Mechanical Data** 

Case: SOT89



#### Ordering Information (Notes 4 & 5)

| Product     | Compliance | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|-------------|------------|---------|--------------------|-----------------|-------------------|
| ZVP4424ZTA  | AEC-Q101   | 24P     | 7                  | 12              | 1,000             |
| ZVP4424ZQTA | Automotive | 24P     | 7                  | 12              | 1,000             |

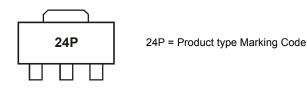
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</li>

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.

5. For packaging details, go to our website at http://www.diodes.com.

# Marking Information







## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                | Symbol           | Value | Unit |
|-------------------------------|------------------|-------|------|
| Drain-Source Voltage          | V <sub>DSS</sub> | -240  | V    |
| Gate-Source Voltage           | V <sub>GSS</sub> | ±40   | V    |
| Continuous Drain Current      | ID               | -200  | mA   |
| Pulsed Drain Current (Note 8) | I <sub>DM</sub>  | -1.0  | A    |

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

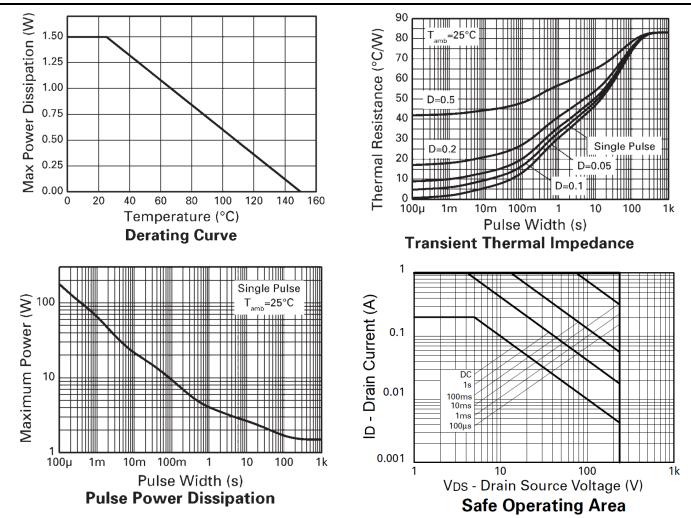
| Characteristic                          | Symbol   | Value                             | Unit        |      |
|---|----------|-----------------------------------|-------------|------|
| Dewer Dissinction                       | (Note 6) | D                                 | 1.5         | W    |
| Power Dissipation                       | (Note 7) | P <sub>D</sub>                    | 2.6         | W    |
| Thermal Desistance Junction to Ambient  | (Note 6) | D                                 | 83.3        | °C/W |
| Thermal Resistance, Junction to Ambient | (Note 7) | R <sub>0JA</sub>                  | 47.4        | °C/W |
| Thermal Resistance, Junction to Leads   | (Note 9) | R <sub>θJL</sub>                  | 3.64        | °C/W |
| Operating and Storage Temperature Range |          | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | С°   |

Notes:

7. For a device surface mounted on FR4 PCB measured at  $t \le 10$  sec. 8. Repetitive rating - 25mm x 25mm FR4 PCB, D = 0.02, pulse width 300µs – pulse width limited by maximum junction temperature.

9. Thermal resistance from junction to solder-point (at the end of the drain lead).

#### Thermal Characteristics



<sup>6.</sup> For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.





## Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic                              | Symbol              | Min   | Turn | Mox  | Unit | Test Condition   |  |
|---|---------------------|-------|------|------|------|--|--|
| OFF CHARACTERISTICS                         | Symbol              | Min   | Тур  | Max  | Unit | Test Condition   |  |
|   | -                   |       | г    | r    |      |  |  |
| Drain-Source Breakdown Voltage              | BV <sub>DSS</sub>   | -240  | —    | —    | V    | $I_D$ = -1mA, $V_{GS}$ = 0V  |  |
| Zero Gate Voltage Drain Current             |                     | —     | —    | -10  | μA   | V <sub>DS</sub> = -240V, V <sub>GS</sub> = 0V                          |  |
|   | IDSS                |       |      | -100 | μA   | V <sub>DS</sub> = -190V, V <sub>GS</sub> = 0V, T <sub>A</sub> = +125°C |  |
| Gate-Source Leakage                         | I <sub>GSS</sub>    | _     | _    | ±100 | nA   | $V_{GS}$ = ±40V, $V_{DS}$ = 0V   |  |
| ON CHARACTERISTICS                          |                     |       |      |      |      |  |  |
| On state Drain Current (Note 10)            | I <sub>D(on)</sub>  | -0.75 | -1.0 | _    | Α    | V <sub>DS</sub> = -10V, V <sub>GS</sub> = -10V                         |  |
| Gate Threshold Voltage                      | V <sub>GS(th)</sub> | -0.7  | -1.4 | -2.0 | V    | $I_D$ = -1mA, $V_{DS}$ = $V_{GS}$                                      |  |
| Statia Drain Source On Desistence (Note 10) |                     | _     | 7.1  | 9    | Ω    | V <sub>GS</sub> = -10V, I <sub>D</sub> = -200mA                        |  |
| Static Drain-Source On-Resistance (Note 10) | R <sub>DS(on)</sub> |       | 8.8  | 11   |      | V <sub>GS</sub> = -3.5V, I <sub>D</sub> = -100mA                       |  |
| Forward Transconductance (Notes 10 & 12)    | g <sub>fs</sub>     | 125   | _    | _    | mS   | V <sub>DS</sub> = -10V, I <sub>D</sub> = -200mA                        |  |
| DYNAMIC CHARACTERISTICS (Note 12)           |                     |       |      |      | _    |  |  |
| Input Capacitance                           | Ciss                | _     | 100  | 200  |      |  |  |
| Output Capacitance                          | Coss                | _     | 18   | 25   | pF   | V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V<br>f = 1.0MHz             |  |
| Reverse Transfer Capacitance                | Crss                | _     | 5    | 15   | 1    |  |  |
| Turn-On Delay Time (Note 11)                | t <sub>d(on)</sub>  |       | 8    | 15   |      | V <sub>DD</sub> = -50V, I <sub>D</sub> = -250mA                        |  |
| Rise Time (Note 11)                         | t <sub>f</sub>      | _     | 8    | 15   |      |  |  |
| Turn-Off Delay Time (Note 11)               | t <sub>d(off)</sub> | _     | 26   | 40   | ns   | $V_{\text{GEN}} = -10V$  |  |
| Fall Time (Note 11)                         | tf                  | _     | 20   | 30   | 1    |  |  |

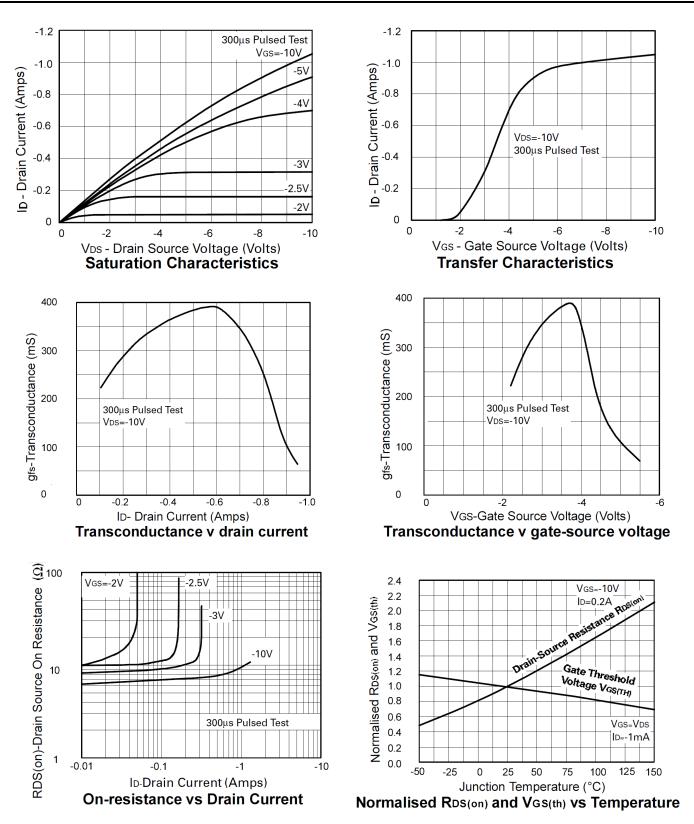
Notes:

Measured under pulsed conditions. Pulse width = 300µs. Duty cycle ≤ 2%.
Switching characteristics are independent of operating junction temperature.
For design aid only, not subject to production testing.





# **Typical Characteristics**

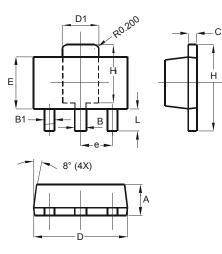






## **Package Outline Dimensions**

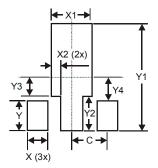
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



| SOT89                |          |      |  |  |
|----------------------|----------|------|--|--|
| Dim                  | Min      | Max  |  |  |
| Α                    | 1.40     | 1.60 |  |  |
| В                    | 0.44     | 0.62 |  |  |
| B1                   | 0.35     | 0.54 |  |  |
| С                    | 0.35     | 0.44 |  |  |
| D                    | 4.40     | 4.60 |  |  |
| D1                   | 1.62     | 1.83 |  |  |
| Е                    | 2.29     | 2.60 |  |  |
| e                    | 1.50 Typ |      |  |  |
| Н                    | 3.94     | 4.25 |  |  |
| H1                   | 2.63     | 2.93 |  |  |
| L                    | 0.89     | 1.20 |  |  |
| All Dimensions in mm |          |      |  |  |

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Х          | 0.900         |
| X1         | 1.733         |
| X2         | 0.416         |
| Y          | 1.300         |
| Y1         | 4.600         |
| Y2         | 1.475         |
| Y3         | 0.950         |
| Y4         | 1.125         |
| C          | 1.500         |





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